

ABSTRACT

A package comprising a package interposer, a first integrated device coupled to the package interposer, a second integrated device coupled to the package interposer, a dummy silicon structure located laterally between the first integrated device and the second integrated device, and a second encapsulation layer coupled to the package interposer, wherein the encapsulation layer at least partially encapsulates the first integrated device, the second integrated device and the dummy silicon structure. The package interposer comprises a first metallization portion; a second metallization portion; a first passive device located between the first metallization portion and the second metallization portion; and a first encapsulation layer located between the first metallization portion and the second metallization portion.